

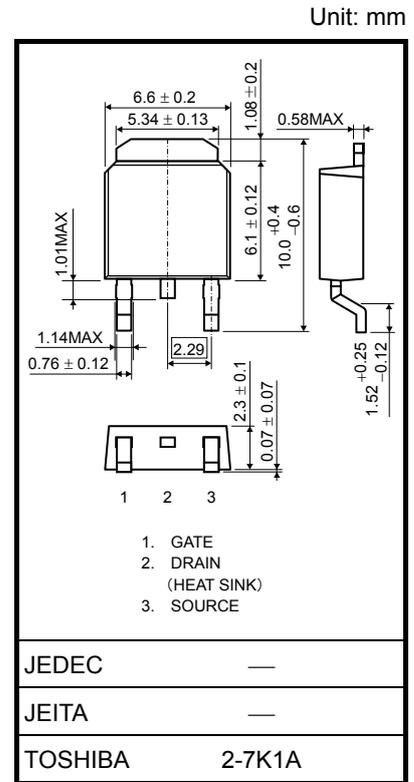
# TK5P50D

## Switching Regulator Applications

- Low drain-source ON-resistance:  $R_{DS(ON)} = 1.3 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 3.0 S$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A$  (max) ( $V_{DS} = 500 V$ )
- Enhancement-mode:  $V_{th} = 2.4$  to  $4.4 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	500	V
Gate-source voltage		$V_{GSS}$	$\pm 30$	V
Drain current	DC (Note 1)	$I_D$	5	A
	Pulse ( $t = 1 ms$ ) (Note 1)	$I_{DP}$	20	
Drain power dissipation ( $T_c = 25^\circ C$ )		$P_D$	80	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	128	mJ
Avalanche current		$I_{AR}$	5	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	8	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ C$



Weight : 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

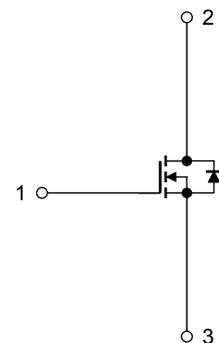
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.56	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	125	$^\circ C/W$

Note 1: Please use devices on conditions that the channel temperature is below  $150^\circ C$ .

Note 2:  $V_{DD} = 90 V, T_{ch} = 25^\circ C$  (initial),  $L = 8.67 mH, R_G = 25 \Omega, I_{AR} = 5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



Start of commercial production  
2009-12